

IN THE CLAIMS:

Claims 1-16 and 37-48 were previously cancelled. Claims 33 and 34 have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1.-16. (Cancelled)

17. (Original) A method of forming a double-sided capacitor having increased capacitance, comprising:  
forming a first opening in a first insulating layer on a semiconductor wafer;  
forming a first sacrificial liner along sidewalls of the first opening;  
forming a sacrificial plug adjacent to the first sacrificial liner, the sacrificial plug formed from a material having a different etch selectivity than a material used in the first sacrificial liner;  
forming a second insulating layer over the first insulating layer;  
forming a second opening in the second insulating layer, the second opening in substantial alignment with the first opening;  
forming a second sacrificial liner along sidewalls of the second opening;  
removing the sacrificial plug;  
forming a first conductive layer over the first and second sacrificial liners, the first conductive layer having a first surface and a second surface, wherein the first surface of the first conductive layer contacts the first and second sacrificial liners;  
selectively removing the first and second sacrificial liners to expose the first surface of the first conductive layer;  
forming a dielectric layer over the first and second surfaces of the first conductive layer; and  
forming a second conductive layer over the dielectric layer.

18. (Previously presented) The method of claim 17, wherein forming the first sacrificial liner along sidewalls of the first opening comprises forming the first sacrificial liner from a material selected from the group consisting of titanium nitride, polysilicon, and hemispherical grain polysilicon.

19. (Previously presented) The method of claim 17, wherein forming the first sacrificial liner along sidewalls of the first opening comprises depositing the first sacrificial liner by chemical vapor deposition.

20. (Previously presented) The method of claim 17, wherein forming the first sacrificial liner along sidewalls of the first opening comprises forming the first sacrificial liner from titanium nitride.

21. (Previously presented) The method of claim 20, wherein forming the sacrificial plug adjacent to the first sacrificial liner comprises forming the sacrificial plug from polysilicon or hemispherical grain polysilicon.

22. (Previously presented) The method of claim 17, wherein forming the first sacrificial liner along sidewalls of the first opening comprises forming the first sacrificial liner from polysilicon or hemispherical grain polysilicon.

23. (Previously presented) The method of claim 22, wherein forming the sacrificial plug adjacent to the first sacrificial liner comprises forming the sacrificial plug from titanium nitride.

24. (Previously presented) The method of claim 17, wherein forming the second sacrificial liner along sidewalls of the second opening comprises forming the second sacrificial liner from a material selected from the group consisting of titanium nitride, polysilicon, and hemispherical grain polysilicon.

25. (Original) The method of claim 17, wherein removing the sacrificial plug comprises removing the sacrificial plug without removing the first and second sacrificial liners.

26. (Original) The method of claim 25, wherein removing the sacrificial plug comprises removing the sacrificial plug using a solution of hydrogen peroxide and sulfuric acid or a solution of tetramethylammonium hydroxide.

27. (Original) The method of claim 17, wherein selectively removing the first and second sacrificial liners to expose the first surface of the first conductive layer comprises removing the first and second sacrificial liners using a solution of hydrogen peroxide and sulfuric acid or a solution of tetramethylammonium hydroxide.

28. (Original) The method of claim 17, wherein selectively removing the first and second sacrificial liners to expose the first surface of the first conductive layer comprises removing the first and second sacrificial liners without damaging exposed components on the semiconductor wafer.

29. (Original) The method of claim 17, wherein selectively removing the first and second sacrificial liners to expose the first surface of the first conductive layer comprises removing the first and second sacrificial liners without removing the first conductive layer.

30. (Original) The method of claim 17, wherein selectively removing the first and second sacrificial liners to expose the first surface of the first conductive layer comprises forming an open space adjacent to the first surface of the first conductive layer.

31. (Previously presented) The method of claim 17, wherein forming the first conductive layer over the first and second sacrificial liners comprises forming the first conductive layer from titanium nitride or polysilicon.

32. (Previously presented) The method of claim 17, wherein forming the dielectric layer over the first and second surfaces of the first conductive layer comprises depositing an insulative material over the first and second surfaces of the first conductive layer.

33. (Currently amended) The method of claim 30, further comprising increasing a thickness of the open space by removing at least a portion of each of the first and second insulating layers.

34. (Currently amended) The method of claim 33, wherein removing the at least a portion of each of the first and second insulating layers comprises etching the at least a portion of each of the first and second insulating layers using a solution of hydrogen fluoride.

35. (Previously presented) The method of claim 17, wherein forming the dielectric layer over the first and second surfaces of the first conductive layer comprises depositing an insulative material over the first and second surfaces of the first conductive layer.

36. (Previously presented) The method of claim 17, wherein forming the second conductive layer over the dielectric layer comprises forming a top electrode of the double-sided capacitor.

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37.-48. (Cancelled)